



Synthesis and Characterization of ZrO₂:ZnO Nanoparticles Prepared by Laser **Induced Plasma**

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| Article's Information | Abstract | |
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| Received: 10.07.2023 Accepted: 29.10.2023 Published: 01.12.2023 | In this research, we looked at how laser energy affected the struct and optical characteristics of ZrO ₂ :ZnO thin films at mixing ratios 0.2, 0.3 and 0.4) that were applied on glass slides using the pulse I deposition technique (PLD). Nd:YAG laser was utilized wit wavelength of 1064 nm, a pulse width of 9 ns, and an energy of 320 The X-ray diffraction patterns revealed that all the films has | |
| Keywords: Laser induced Plasma ZrO ₂ :ZnO XRD AFM UV-VIS spectroscopy | polycrystalline hexagonal crystal structure. AFM was used to measure the topography of the film's surface, and the results revealed that the average roughness and grain size increased. After analyzing the optical characteristics of each film, it was discovered that the absorption coefficient in the 200–1000 nm wavelength range increases at 320 mJ of laser energy and that the optical energy gap value for indirect permitted transitions decreases between 3.58 and 3.4 eV. | |
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1. Introduction

In 1960, one of the best and most cheap techniques for producing oxides, deposits of minerals, and semiconductors in a variety of technical applications was pulse laser deposition [1]. Since late 1987, when T. Venkatesan and coworkersone of the authors of this issue-discovered that the extreme nonequilibrium conditions produced by pulsed laser melting of YBaCuO permitted the in-situ formation of thin films of this high temperature (T_c) transition superconducting material, research on materials grown by pulsed laser deposition, or PLD, has seen phenomenal growth. Since then, PLD has become the main producing method for high-quality superconducting thin films in large quantities for use in devices and research[2]. Thin films of conductive oxide (TCO), like zinc oxide [3], have low resistance and excellent optical transmittance. ZnO is a semiconductor material with several uses due to its large and direct energy gap of 3.3 eV, which is close to the UV area. Numerous optoelectronic applications of ZnO may be found in solar cells, spintronics [4], [5], laser diodes (LDs), and light-emitting diodes (LEDs)[6]. Due to

qualities, physical commonly known as zirconia, is used in a variety of products, including fuel cells [15], gas sensors [16], optoelectronics, catalysts , and corrosionresistant materials [19]. ZrO₂ has a band gap of 5 eV and is a significant luminous material with

evaporation[8].

internal structural faults like oxygen and zinc

gaps, or interstitial conditions in a lattice, ZnO is

an n-type semiconductor material [7]. ZnO nanostructured thin films have been produced

using a variety of methods, including thermal

sputtering[9], chemical vapor [10], and ion-beam

assisted [11]. The laser-induced plasma (LIP)

approach is one of the most popular and alluring

methods for creating nanostructured thin films

with a particular property [12]. Metal oxide

materials can be generated as high-quality

nanofilms utilizing the laser-induced plasma (LIP)

process .The benefit of LIP over their techniques is

that multilayered films made of various materials

may be produced very easily. Although zirconium

oxide has numerous applications, large band gap

metal oxide nanoparticles have caught the interest

of scientists. Due to its superior chemical and

zirconium oxide

sputtering

8.

 (ZrO_2)

magnetron

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good optical transparency . Its high surface area and abundance of oxygen vacancies make it a possible option for photocatalytic applications [21].ZrO₂ nanostructures can be made using a variety of techniques, including sol-gel[22], hydrothermal [23], combustion [24], and coprecipitation [25,26].

2. Experimental Details:

The four ZrO₂:ZnO nanostructure samples in the current work are precipitated on glass using micropowders of zinc oxide and zirconium oxide that are accessible and have a purity of 99.99%. Zirconium oxide powder and zinc powder were mixed in a variety of weight ratios according to the following formula:

$$WZrO_2 + ZnO \rightarrow WZrO_2(x) + WZnO(1-x) \dots (1)$$



Figure 1: Schematic representation of a system for pulsed laser deposition

The results for Mixing between ZrO₂ & ZnO (W_{ZrO2} $_{+ ZnO} = 2gm$), (0.22 from zirconium oxide and 1.77 from zinc oxide were mixed for a ratio of 0.1; than 0.43 from zirconium oxide and 1.56 from zinc oxide were mixed for a ratio of 0.2). A weight ratio of 0.64 from zirconium oxide and 1.35 from zinc oxide were mixed for a ratio of 0.3; than 0.85 from zirconium oxide and 1.14 from zinc oxide were mixed for a ratio of 0.4. The substrates were positioned inside the chamber with a 10 cm gap between them and the target, and then a steady 150 watt power source was used during the twohour deposition procedure. A basic vacuum pressure of 10⁻⁵ bars was used within the chamber to conduct the deposition operation. PLD was used in this work to deposit (ZrO₂:ZnO) films. By aiming the laser at the target (the pellet), which causes the material to evaporate and grow on the substrate, thin film growth was accomplished. The Nd:YAG laser, which has a wavelength of 1064 nm, was utilized for the growth process of films.

The duration and energy of the laser pulses, among other laser parameters, affect the evaporation process [27]. The experiment was carried out in a vacuum chamber at a pressure of 2.5×10^{-2} mbar. Using a hydraulic piston of the SPECAC type, the (ZrO₂:ZnO) target was created using 6 Pa of pressure over the course of 10 minutes, yielding a disc with a (2.5 cm) diameter and (200 nm) thickness. This research examined the structural and morphological characteristics of thin films made of ZrO₂:ZnO on glass slides. Nd:YAG laser with 200 pulses per shot, 320 mJ of energy, (f = 6 Hz) of frequency, and 1064 nm wavelength (λ) . The angle formed by the incident Nd:YAG SHG Q-switching laser beam and the target surface is approximately 45 degrees. As shown in Fig. 1, the first vacuum system is a rotating vacuum system with two stages, a pressure and temperature gauge, and a vacuum chamber. Through the use of X-ray diffraction (XRD) and atomic force microscopy (AFM), the crystal structure and morphology were investigated. To ascertain the films' optical ultraviolet characteristics, spectroscopy (UV)analysis was also performed.

3.Results and discussion:

3.1 - X-ray diffraction examination: The crystalline structure and grain size of the (ZrO₂:ZnO) films produced by PLD procedures were determined using X-ray diffraction (XRD). Through the use of Scherrer's equation, the grain size (D) was calculated [28][29];

$$D = \frac{K \cdot \lambda}{\beta \, Cos(\theta_{\beta})} \quad \dots (2)$$

Where β full width at half maximum (FWHM), θ_{β} Bragg's angle, and λ is X-ray wavelength (1.54 A^o), where 0.94 is assumed to be a constant for k. The crystalline structure and grain size of the ZnO and ZrO_2 produced by PLD procedures were determined using X-ray diffraction (XRD). The use of the X-ray diffraction technique revealed that polycrystalline structures were used in the preparation of all thin films. The XRD patterns for ZnO powder are shown in Figure 2, which demonstrate the material's hexagonal structure and diffraction peaks at crystalline hkl (100), (002), (101), (102), (110), (103), (200), (112), and (201). This correspond to $2\theta = 31.8^{\circ}$, 34.4° , 36.3° , 47.5°, 56.6°, 62.8°, 66.4°, 67.9° and 69.1°, and the average crystallite size is 39 nm. The outcomes are fairly consistent with the standard values of the supplied data (JCPDS No. 98-004-1488). Using

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Scherrer's equation, the experimental inter-plane gap and crystal size were determined.

It may contain subheadings, which are divided into numbered subsections.



Figure 2. X-ray pattern of ZnO Powder

While the XRD patterns for ZrO_2 powder are shown in Figure 3, which show that the material has a hexagonal structure with diffraction peaks at crystalline hkl (110), (002), (101), (012), (110), (113), (103), (112) and (201), which correspond to $2\theta = 31.8^{\circ}$, 34.6° , 36.35° , 47.7° , 56.65° , 63.1° , 66.4° , and 68.1° , and the average crystallite size is 33 nm, the outcomes are quite consistent with the normative values of the supplied data (No. 98-008-8320).



Figure 3. X-ray pattern of ZrO₂ Powder

Figure 4 shows the X-ray diffraction of thin ZrO₂:ZnO films that are 200 nm thick at X = 0.1, 0.2, 0.3, and 0.4. Peaks of the material (ZnO) with hkl [(100), (002), (101), (012), (110), (013), (112), and (201)] emerge at $2\theta = 31.8^{\circ}$, 34.5° , 36.3° , 47.7° , 56.75° , 62.9° and 68.05° and peaks of the Zr with hkl [(111), (200), (202), (311)] and emerge at $2\theta = 30.3^{\circ}$, 35.3° , 50.5° , 60.3° , and 63°

and the average crystallite size for ZnO at (0.1, 0.2, 0.2)0.3 and 0.4) is 20.66 nm, 20.79 nm, 21.83, and 22.78 nm, and the average crystallite size for ZrO₂ with the same proportions is 21.10 nm and 22 nm, which are identical to JCPDS card No. (98-004-1488) for ZnO and card No. (98-0088320) for ZrO₂. Crystal development begins with a spike in doping. There is no doubt that crystallization is developing, and because there are numerous peaks and a hexagonal pattern, it appears that the sedimentary models have a polycrystalline structure. From Figure 4, we conclude that the average crystal size increases with increasing ZrO₂:ZnO ratios.



Figure 4. X-ray diffraction pattern for mix ZrO₂:ZnO

3.2 Atomic force microscopy:

Atomic force microscopy (AFM) was used to examine the surface morphology of the thin film that had been deposited. Figure 5 displays the acquired AFM images for both pure and doped thin films. The morphological characteristics of the deposited films can be predicted using image analysis; for example, the films may have grains of varying sizes, uneven forms, and separation. It can be concluded from a comparison of images taken at various zirconium oxide concentrations that the concentration of zirconium oxide significantly improved the morphological qualities of the films. When ZrO_2 doping ratios and grain sizes are raised, the roughness values and root mean square RMS rise, which causes the film's surface to become rough [[28],[29].

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Figure 5. Images of ZrO_2 : ZnO thin films deposited with different concentrations of (a) 0.1 (b) 0.2 (c) 0.3 and (d) 0.4.

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The average diameter, root mean square, and average roughness of ZrO_2 :ZnO thin films are shown in Table 4 as AFM parameters. Laser pulses were used to deposit the thin layers on the glass substrate.

| Sample | Rat io | Avg. Diame ter (nm) | Root Mean Sq. (nm) | Avg. Roughness (nm) |
|--------------|-----------|------------------------------|-----------------------|------------------------|
| ZrO2:Z nO | 0.1 | 74.04 | 13.5 | 10.1 |
| | 0.2 | 78.7 | 14.4 | 11.3 |
| | 0.3 | 89.06 | 17.9 | 14.4 |
| | 0.4 | 91.61 | 20.6 | 16.4 |

Table 1. The average roughness, root mean square, and average grain size for ZrO₂:ZnO thin films.

3.3 The absorption coefficient:

An UV-Vis spectrophotometer with a double beam was used to determine the optical characteristics. Taiwan's (MetertechSP8001). Tauc's formula for direct transition was used to graphically estimate the optical band gap [30].

$$\begin{array}{l} \alpha h \nu \propto \left(h \nu - E_g \right)^n \dots (3) \\ (\alpha h \nu)^2 \propto A \left(h \nu - E_g \right)^n \dots (4) \end{array}$$

where α is the absorption coefficient, h is the Planck constant, v is the frequency of the photon, E_g is the optical energy gap, and n is a constant that is dependent on the nature of the transition. A is a constant that relies on the nature of the material. PLD, or pulse laser deposition, was employed. At laser energy E = 320 mJ, the absorption coefficient (a) varies as a function of wavelength in all films of Zinc oxide doped with Zirconium Oxide ZrO_2 :ZnO (X = 0.1, 0.2, 0.3 and 0.4), as shown in Figure 6. According to the findings, raising the doping ratio caused all coefficient absorption values for the state reconstitution to increase significantly. Considering that donor levels are produced in the energy gap just outside the conduction band [30].

3.4 Calculation of the optical energy gap (Eg):

The amount to which thin films produced during the production of hybrid joints, reagents, and solar cells may be used depends critically on the optical energy gap. In the event, a diagram illustrating the link was plotted as a function of photon energy (*hv*), as seen in Figure 7, where the intersection of the straight portion of the curve with the photon energy axis $(\alpha hv)^2 = 0$) represents the magnitude of the direct visual energy gap. Figure 7 displays the optical energy gap for the direct ZrO₂:ZnO film transport that is permitted as well as the optical energy gap for indirect ZrO_2 :ZnO films' permissible transport at X = 0.1, 0.2, 0.3, and 0.4.



Figure 6. The absorption coefficient for pure ZrO2:ZnO (X =0.1, 0.2, 0.3, and 0.4) varies with wavelength.



Figure 7. The dependence of $(\alpha h\nu)^{1/2}$ on photon energy (hv) for ZrO₂:ZnO thin films produced on glass substrates.

The results show that the energy gap is an indirect allowed gap, and the value of the absorption coefficient is equal to $\alpha > 10^4$, demonstrating that the energy gap is 2.0 eV for the permitted indirect transmission of a membrane (ZrO₂:ZnO). This conclusion is consistent with the findings of earlier studies. The decrease in the optical bandgap is caused by an increase in ZrO₂:ZnO composition in various preparation methods. According to Mohammed et al. (2022)[31], the aggregation in the samples might have been responsible for the redshift and decrease of the band gap energy. Table 2 lists all values in tabular form.

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Table 2. The energy gap of ZrO2:ZnO for (X=0.1,0.2,0.3 and 0.4) deposited.

| Sample (X mixing ratio) | E _g (eV) |
|-------------------------|---------------------|
| 0.1 | 3.58 |
| 0.2 | 3.5 |
| 0.3 | 3.46 |
| 0.4 | 3.4 |

3.5 Conclusions

The ZrO₂:ZnO the film was prepared using an Nd:YAG laser with a fundamental wavelength of 1064 nm. on the glass substrate. The X-ray findings revealed that all thin films are polycrystalline and have a hexagonal structure with direction dominance (111). The results of AFM show that the higher the percentage of doping, the increase in grain size. As for the properties measurements, it was found that the absorption coefficient increase as the percentage of doping increases. Whereas the energy gap, on the other hand, decreases with the rate of doping increases.

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